

BAS16L, SBAS16L

Switching Diode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	100	V
Peak Forward Current	I_F	200	mA
Non-Repetitive Peak Forward Surge Current 60 Hz	$I_{FSM(surge)}$	500	mA
Repetitive Peak Forward Current (Note 3)	I_{FRM}	1.0	A
Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^\circ\text{C}$ prior to surge)	I_{FSM}		A
$t = 1 \mu\text{s}$		36.0	
$t = 10 \mu\text{s}$		18.0	
$t = 100 \mu\text{s}$		6.0	
$t = 1 \text{ ms}$		3.0	
$t = 1 \text{ s}$		0.7	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

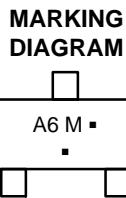
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. $\text{FR-5} = 1.0 \times 0.75 \times 0.062 \text{ in.}$
2. Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.
3. Square Wave, $f = 40 \text{ kHz}$, $PW = 200 \text{ ns}$
Test Duration = 60 s, $T_J = 25^\circ\text{C}$ prior to surge.



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A6 = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS16LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BAS16LT3G	SOT-23 (Pb-Free)	10000/Tape & Reel
SBAS16LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
SBAS16LT3G	SOT-23 (Pb-Free)	10000/Tape & Reel

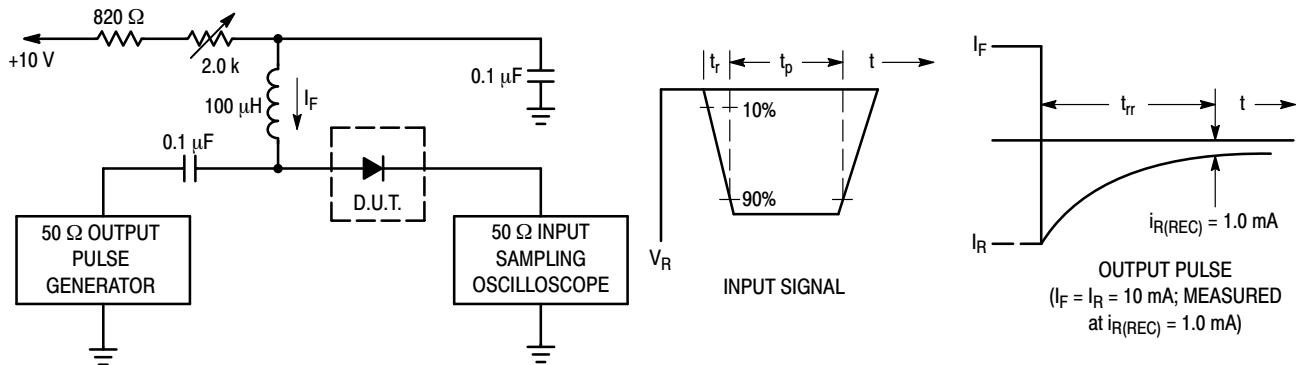
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current ($V_R = 100 \text{ V}$) ($V_R = 75 \text{ Vdc}, T_J = 150^\circ\text{C}$) ($V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$)	I_R	— — —	1.0 50 30	μAdc
Reverse Breakdown Voltage ($I_{BR} = 100 \mu\text{Adc}$)	$V_{(BR)}$	100	—	Vdc
Forward Voltage ($I_F = 1.0 \text{ mA}$) ($I_F = 10 \text{ mA}$) ($I_F = 50 \text{ mA}$) ($I_F = 150 \text{ mA}$)	V_F	— — — —	715 855 1000 1250	mV
Diode Capacitance ($V_R = 0, f = 1.0 \text{ MHz}$)	C_D	—	2.0	pF
Forward Recovery Voltage ($I_F = 10 \text{ mA}$, $t_r = 20 \text{ ns}$)	V_{FR}	—	1.75	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}$, $R_L = 50 \Omega$)	t_{rr}	—	6.0	ns
Stored Charge ($I_F = 10 \text{ mA}$ to $V_R = 5.0 \text{ Vdc}$, $R_L = 500 \Omega$)	Q_S	—	45	pC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



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TYPICAL CHARACTERISTICS

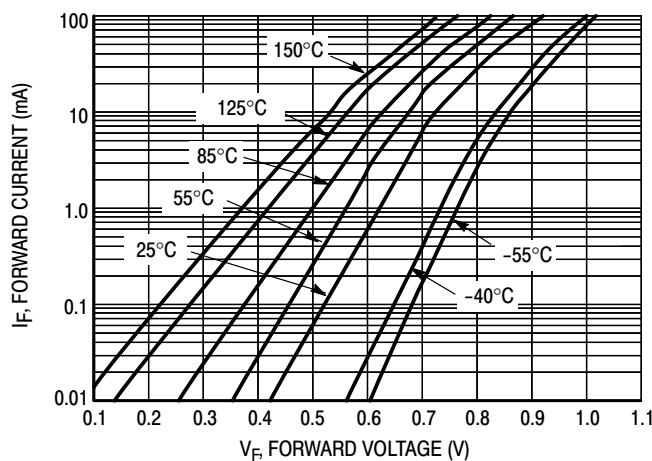


Figure 2. V_F vs. I_F

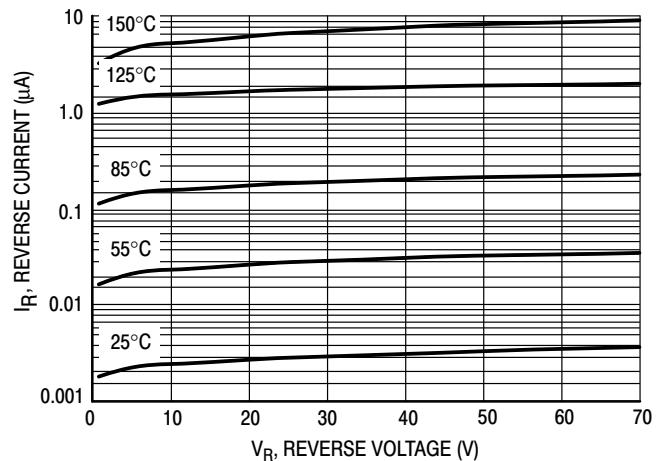


Figure 3. I_R vs. V_R

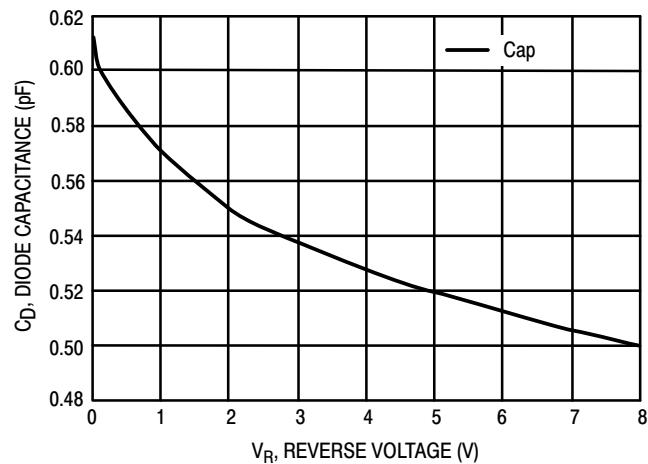
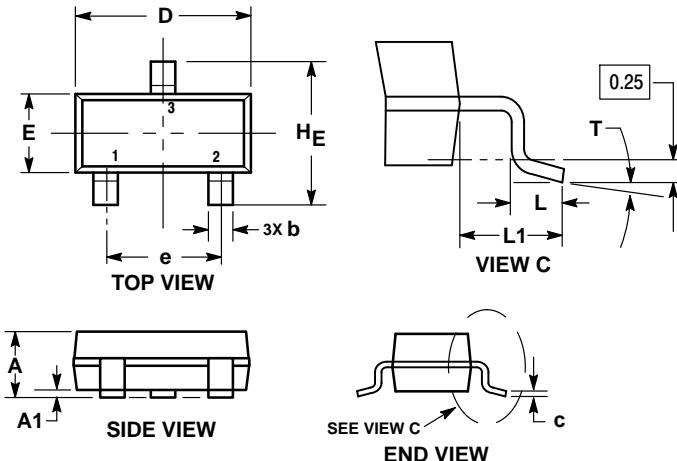


Figure 4. Capacitance

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PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AR



NOTES:

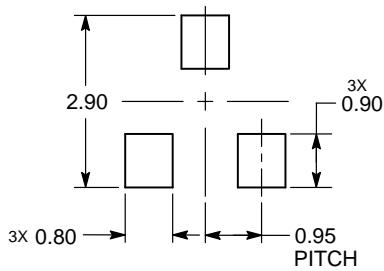
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	—	10°	0°	—	10°

STYLE 8:

1. ANODE
2. NO CONNECTION
3. CATHODE

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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